


 Cite this: *Phys. Chem. Chem. Phys.*, 2023, 25, 25055

Correction: Lone pair driven anisotropy in antimony chalcogenide semiconductors

 Xinwei Wang,^a Zhenzhu Li,^{ab} Seán R. Kavanagh,^{ac} Alex M. Ganose^a and Aron Walsh^{*ab}

DOI: 10.1039/d3cp90185h

 Correction for 'Lone pair driven anisotropy in antimony chalcogenide semiconductors' by Xinwei Wang *et al.*, *Phys. Chem. Chem. Phys.*, 2022, 24, 7195–7202, <https://doi.org/10.1039/D1CP05373F>.

rsc.li/pccp

The authors regret that Fig. 5(b) was incorrect in the original manuscript due to a minor error in the code used for calculating the orientation-dependent radiative limit to photovoltaic conversion efficiency. The corrected figure is shown here. The optical absorption spectra of Sb₂S₃ and Sb₂Se₃ result in a weak orientation-dependent radiative limit of conversion efficiencies. When the film thickness is 500 nm, the difference between the maximum and minimum efficiencies along different directions is 1.31% and 2.40% for Sb₂S₃ and Sb₂Se₃, respectively. The authors note that the correction of Fig. 5(b) does not change the central conclusions of the paper.

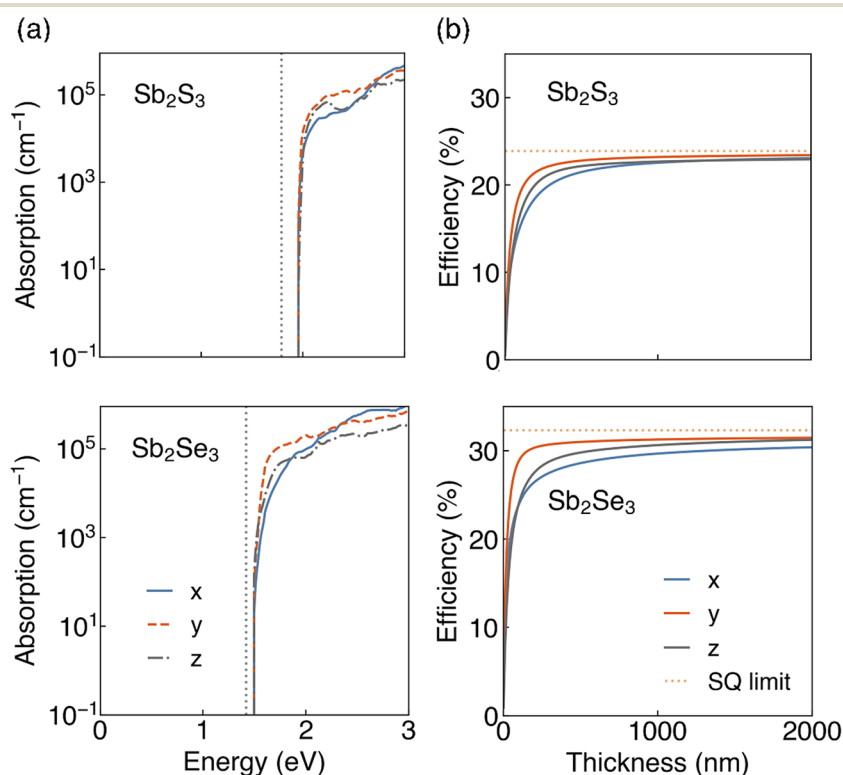


Fig. 5 (a) Calculated optical absorption spectra of Sb₂S₃ and Sb₂Se₃ arising from direct valence to conduction band transitions. The fundamental band gaps are shown in grey dotted lines. (b) Thickness-dependent maximum efficiencies based on the radiative limit of Sb₂S₃ and Sb₂Se₃. x, y and z refer to the direction of the electric polarisation vector of light.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

^a Department of Materials, Imperial College London, Exhibition Road, London SW7 2AZ, UK. E-mail: a.walsh@imperial.ac.uk

^b Department of Materials Science and Engineering, Yonsei University, Seoul 03722, Korea

^c Thomas Young Centre and Department of Chemistry, University College London, 20 Gordon Street, London WC1H 0AJ, UK

